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# FDP75N08A

## N-Channel UniFET™ MOSFET

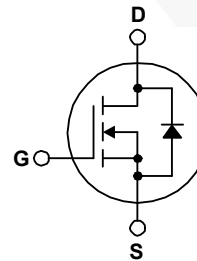
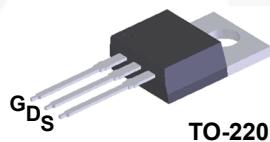
### 75 V, 75 A, 11 mΩ

#### Features

- 75 A, 75 V,  $R_{DS(on)} = 11 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$
- Low Gate Charge (Typ. 145 nC)
- Low Crss (Typ. 86 pF)
- Fast Switching
- Improved dv/dt Capability

#### Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDP75N08A	Unit
$V_{DSS}$	Drain-Source Voltage	75	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	75	A
		47	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	300	A
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1738	mJ
$I_{AR}$	Avalanche Current (Note 1)	75	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	13.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	137	W
	- Derate Above $25^\circ\text{C}$	1.09	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

#### Thermal Characteristics

Symbol	Parameter	FDP75N08A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.91	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP75N08A	FDP75N08A	TO-220	Tube	N/A	50 units

## Electrical Characteristics TC = 25°C unless otherwise noted.

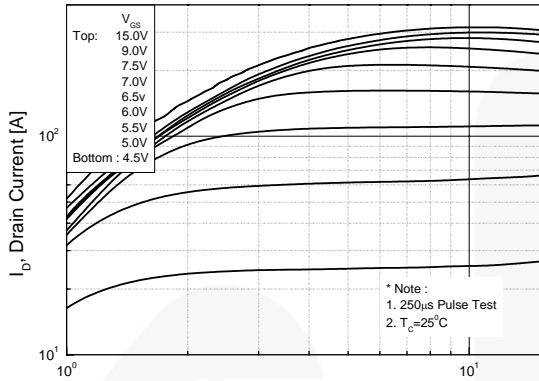
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	75	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to 25°C	--	0.6	--	V/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 37.5\text{ A}$	--	9.4	11	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 37.5\text{ A}$	--	15	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	3437	4468	pF
$C_{oss}$	Output Capacitance		--	738	959	pF
$C_{rss}$	Reverse Transfer Capacitance		--	86	129	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 37.5\text{ V}, I_D = 75\text{ A},$ $R_G = 25\ \Omega$	--	43	95	ns
$t_r$	Turn-On Rise Time		--	212	434	ns
$t_{d(off)}$	Turn-Off Delay Time		--	273	556	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	147	303
$Q_g$	Total Gate Charge	$V_{DS} = 60\text{ V}, I_D = 75\text{ A},$ $V_{GS} = 10\text{ V}$	--	80	104	nC
$Q_{gs}$	Gate-Source Charge		--	20	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	24	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	75	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	300	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 75\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 75\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	62	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	145	--	nC

### Notes:

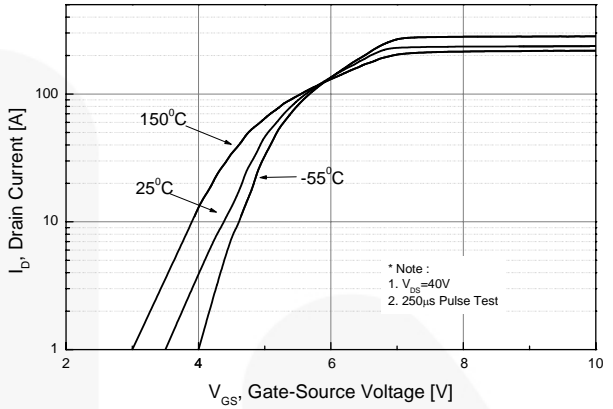
- 1: Repetitive rating; pulse-width limited by maximum junction temperature.
- 2:  $L = 206\ \mu\text{H}, I_{AS} = 75\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
- 3:  $I_{SD} \leq 75\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
- 4: Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

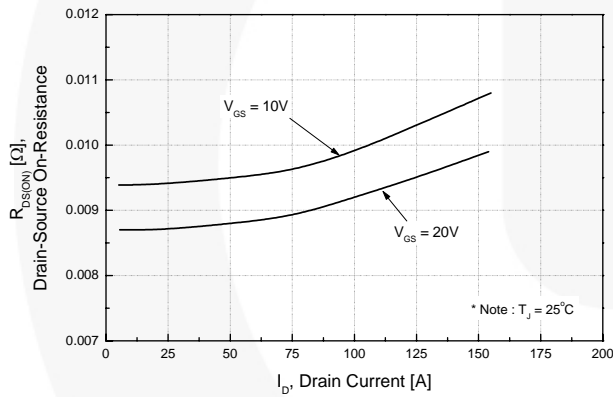
**Figure 1. On-Region Characteristics**



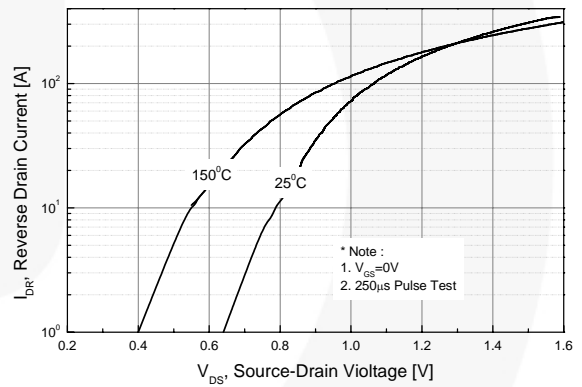
**Figure 2. Transfer Characteristics**



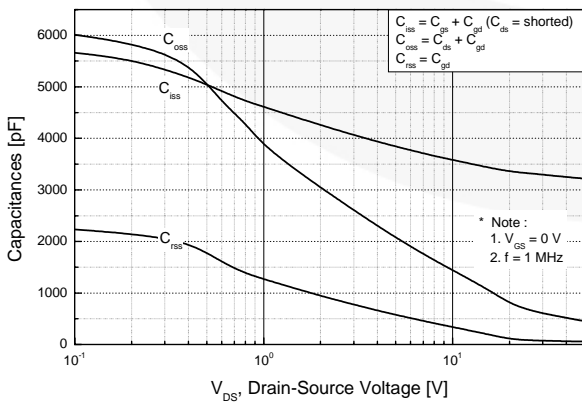
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



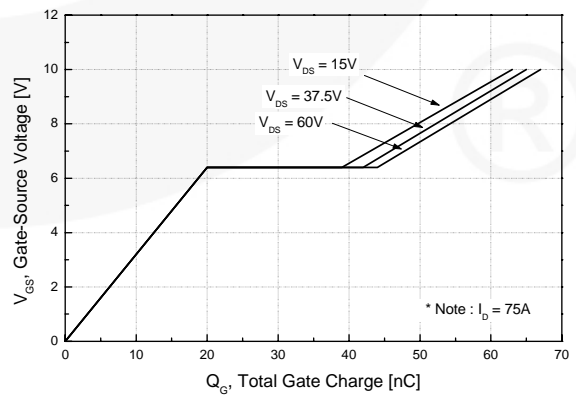
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

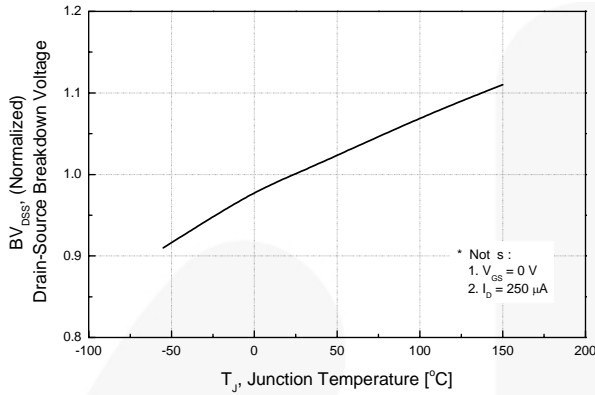


**Figure 6. Gate Charge Characteristics**

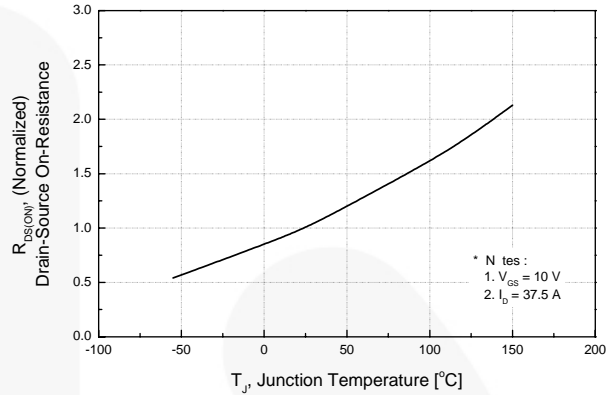


**Typical Performance Characteristics** (Continued)

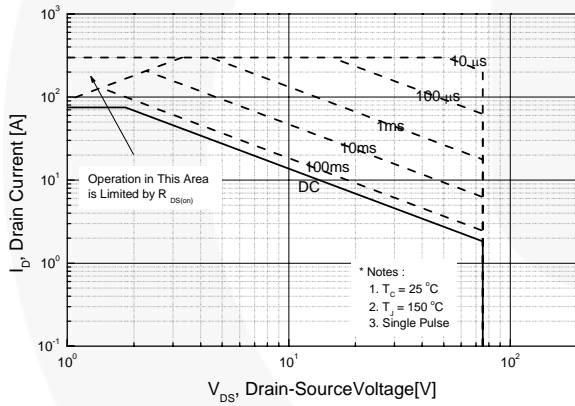
**Figure 7. Breakdown Voltage Variation vs. Temperature**



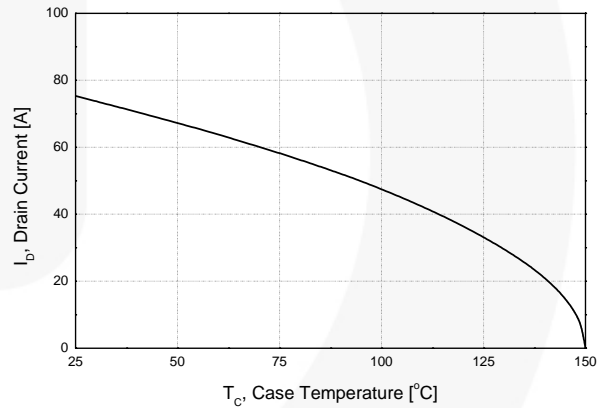
**Figure 8. On-Resistance Variation vs. Temperature**



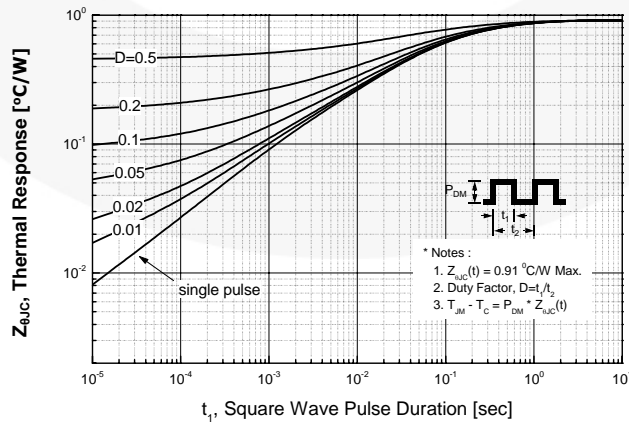
**Figure 9. Maximum Safe Operating Area**



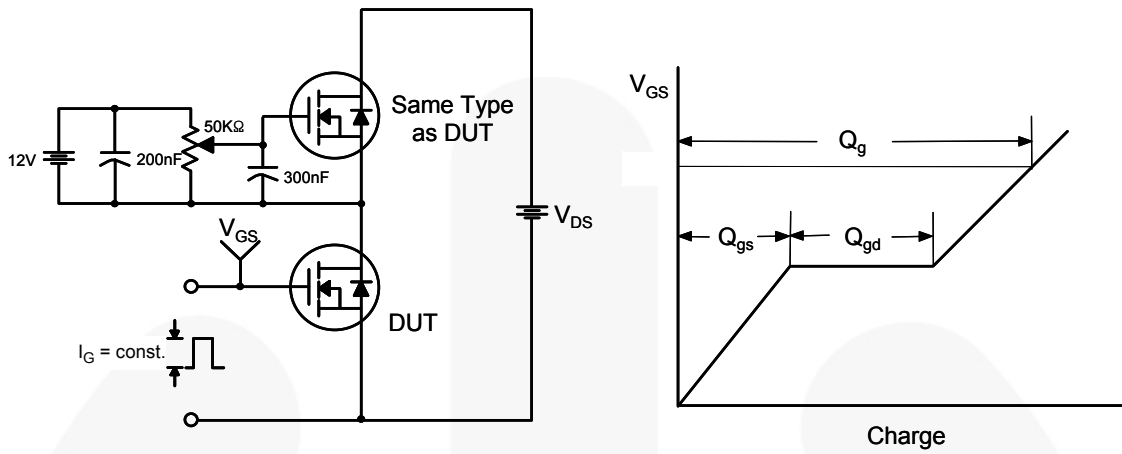
**Figure 10. Maximum Drain Current vs. Case Temperature**



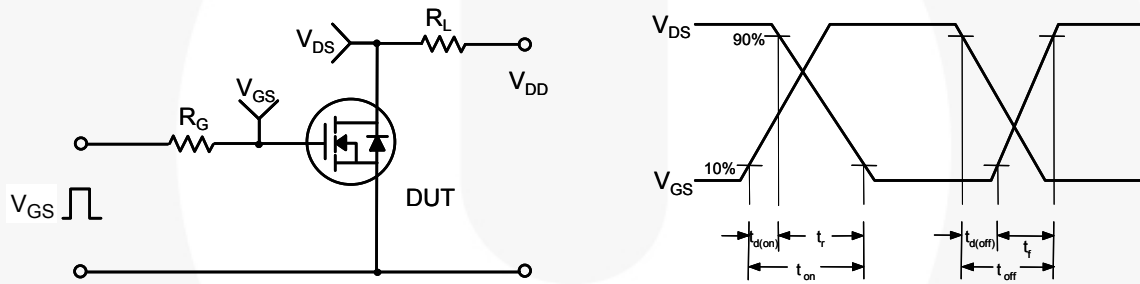
**Figure 11. Transient Thermal Response Curve**



**Figure 12. Gate Charge Test Circuit & Waveform**



**Figure 13. Resistive Switching Test Circuit & Waveforms**



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

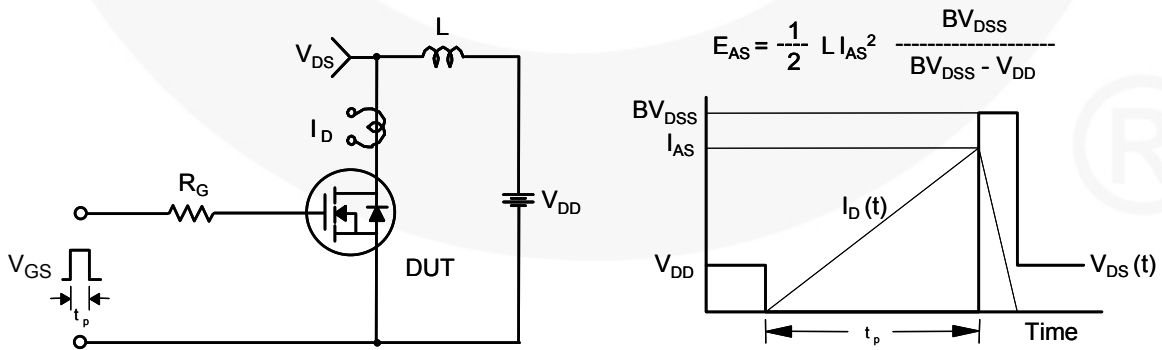
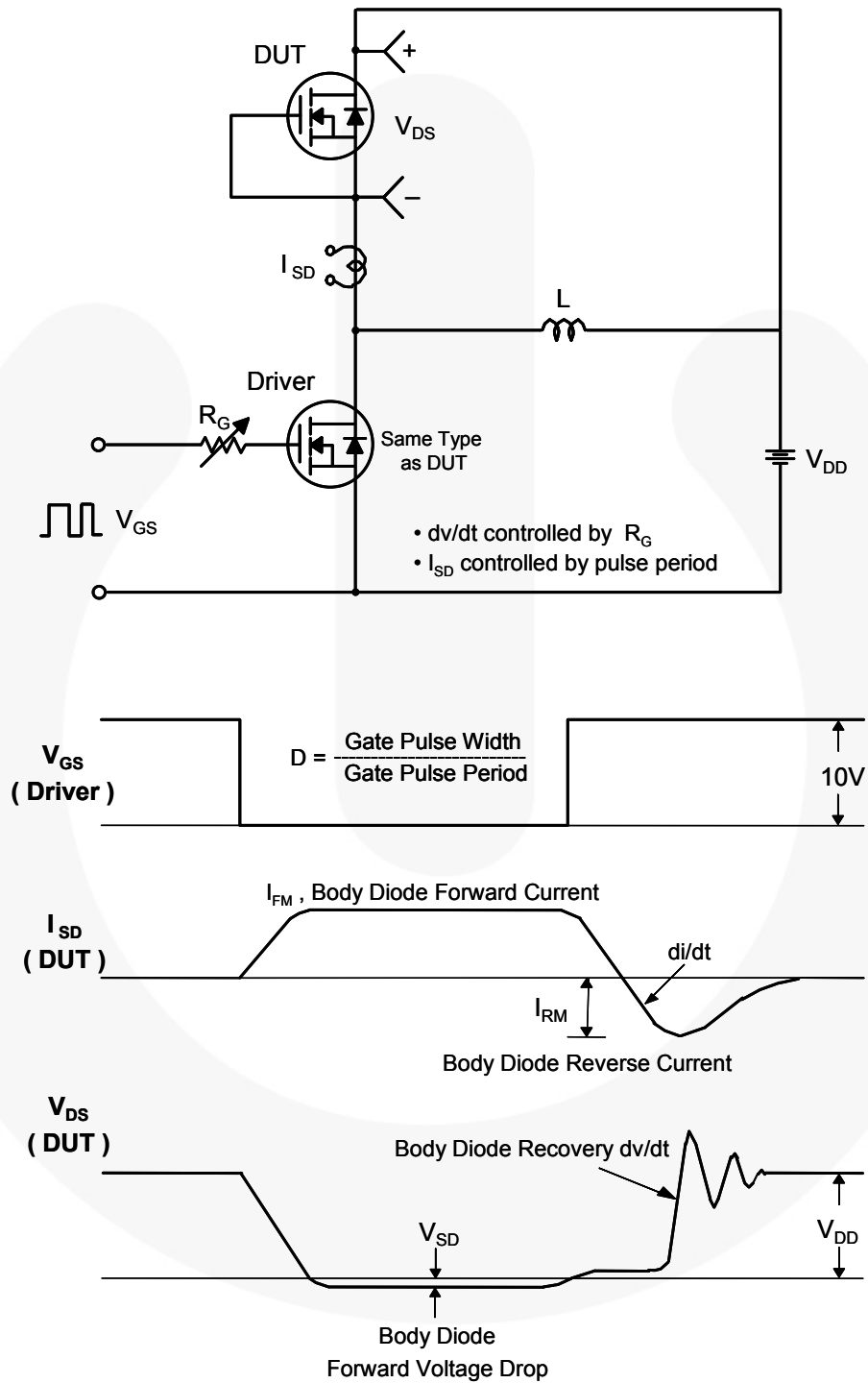


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions



**Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB**

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